

ABSTRACT OF THE DISCLOSURE

A method of forming a cavity between metallic wirings using a polymer capable of revealing a specific heat resistant temperature and a specific heat decomposition temperature by having a specific repeating unit structure and a specific molecular weight range and of readily forming a cavity structure between metallic wirings in, for example, semiconductors. The method comprises a step of coating the surface of a first dielectric film formed on a semiconductor substrate with a cyclic olefin based addition polymer, a step of patterning the cyclic olefin based addition polymer as a void-forming polymer, a step of forming a metallic wiring in the pattern formed on the void-forming polymer, a step of forming a second dielectric film on the void-forming polymer containing a metallic wiring, and a step of removing the void-forming polymer between the multilayered wirings by heating to form a cavity between the metallic wirings.